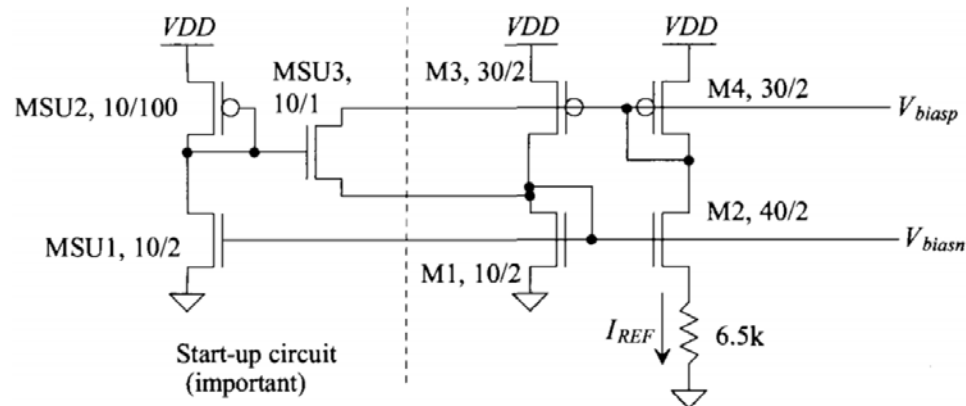


Due: Oct. 15, 2018 6PM. 20% / day will be deducted if you miss the 6 PM Oct. 15 deadline.

### Design of Beta Multiplier Circuit

In this homework, you will design a beta multiplier circuit presented in Lecture 11 which is shown here again. Run a dc simulation for problem 1. For problem 2 and 4, run transient simulations.



The device size above is reference only. You must come up with your own size based on  $V_{DD}=1V$  at TT, 27C. Your simulation results on dc operating point should show M1-M4 are in saturation region.

1. Run a dc simulation with  $V_{DD}=1V$ , Temperature=27C in Typical corner. Using ADE-L window, select Results->Annotate feature to get the dc operating point information as well as the node voltage information in the schematic you have designed. Create a screenshot of this! **(20 points)**
2. Using ADE-XL, run transient simulations for 1 us. Ramp up the power supply from 0V at  $t=0$  to the final voltage ( $V_{DD}=1V$  for example) in 10 ns. Plot the transient waveforms for  $V_{DD}$ ,  $V_{biasn}$ ,  $V_{biasp}$ , drain currents of M1, M2, MSU1, MSU3. Repeat the simulation without the Start-up circuit by connecting the drain of MSU3 to  $V_{DD}$  and the source of MSU3 to GND. Plot the same parameters to compare if there is any difference between with and without the start-up circuit. **(20 points)**
3. From the simulation result, you will get the  $I_{ref}$  in your design for the size you are using. From this, using the expression for  $I_{ref}$  shown in Lecture 11, find out the KP value when  $V_{DD}=1V$ , Temperature=27C. **(10 points)**
4. Using Cadence ADE-XL, simulate the circuit in the following conditions and check if the circuit starts without any problem. Measure the current through M4 ( $I_{ref}$ ) at 1 us and plot it over the following PVT corners.
  - a) Process variation only: TT, SS, FF, SF, FS at  $V_{DD}=1V$  and Temp=27C **(10 points)**
  - b) Supply variation only: 0.8V, 0.9V, 1V, 1.1V, 1.2V at TT & Temp=27C **(10 points)**
  - c) Temperature variation only: -40C, 0C, 25C, 50C, 100C at  $V_{DD}=1V$  and TT **(10 points)**
  - d) All PVT variations (TT, SS, FF, SF, FS,  $V_{DD}=0.9V, 1V, 1.1V$ , Temp=-40, 0, 50, 100C) This will give you a set of 60 simulation results. **(10 points)**
  - e) For the case c) at  $V_{DD}=1$ , TT, plot gm vs. Temp for transistor M1. For this plot, use Tools->Result Browser->TranOP in ADE-XL window and select gm in M1 folder. **(10 points)**

Your goal is to reduce the  $I_{ref}$  variation over PVT. Report the minimum and maximum currents as well as the mean and 1-sigma number for  $I_{ref}$  variation over 60 PVT corner simulations.